MOSFETs Silicon N-channel MOS (U-MOSVII-H)

# TPH2900ENH

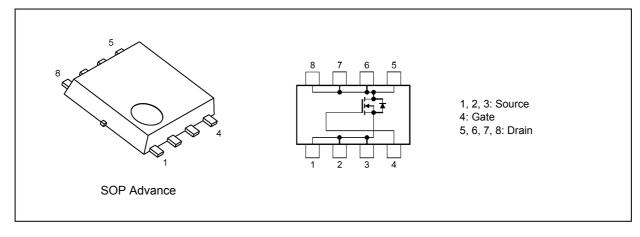
#### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 8.2 \text{ nC}$  (typ.)
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 24 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (4) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 200 \ V)$
- (5) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1.0 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characterist	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	200	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι <sub>D</sub>	36	A
Drain current (DC)	(Continuous)	(Note 1)	Ι <sub>D</sub>	33	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I <sub>DP</sub>	102	
Power dissipation	(T <sub>c</sub> = 25 °C)		PD	78	×
Power dissipation	(t = 10 s)	(Note 3)	PD	2.8	
Power dissipation	(t = 10 s)	(Note 4)	PD	1.6	
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	176	mJ
Avalanche current			I <sub>AR</sub>	33	A
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T <sub>c</sub> = 25 °C)		R <sub>th(ch-c)</sub>	1.60	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	44.6	
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R <sub>th(ch-a)</sub>	78.1	

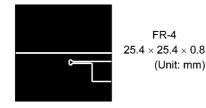
Note 1: Ensure that the channel temperature does not exceed 150 °C.

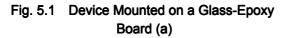
Note 2: Limited by silicon chip capability.

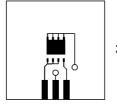
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V\_DD = 60 V, T\_ch = 25 °C (initial), L = 250  $\mu H, I_{AR}$  = 33 A







 $\begin{array}{c} \text{FR-4} \\ \text{25.4} \times \text{25.4} \times \text{0.8} \\ \text{(Unit: mm)} \end{array}$ 

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

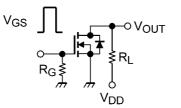
### 6. Electrical Characteristics

### 6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V	_		10	1
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	200		_	V
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	140	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA	2.0		4.0	1
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.5 A		24	29	mΩ

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1700	2200	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	7.0	50	
Output capacitance	C <sub>oss</sub>		_	180	_	
Gate resistance	rg	—	_	4.0	6.0	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	8.0	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	20	_	
Switching time (fall time)	t <sub>f</sub>	]	_	12	_	
Switching time (turn-off time)	t <sub>off</sub>			36	_	



$$\begin{split} V_{DD} &\approx 100 \text{ V} \\ V_{GS} &= 0 \text{ V}/10 \text{ V} \\ I_D &= 16.5 \text{ A} \\ R_L &= 6.06 \Omega \\ R_G &= 4.7 \Omega \\ \text{Duty} &\leq 1 \ \%, \ t_w &= 10 \ \mu\text{s} \end{split}$$

Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

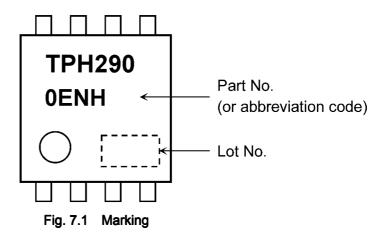
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 100 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 33 \text{ A}$	_	22	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	9.0	_	nC
Gate-drain charge	Q <sub>gd</sub>	]	_	4.4	_	
Gate switch charge	Q <sub>SW</sub>			8.2		

#### 6.4. Source-Drain Characteristics (Ta = 25 °C unless otherwise specified)

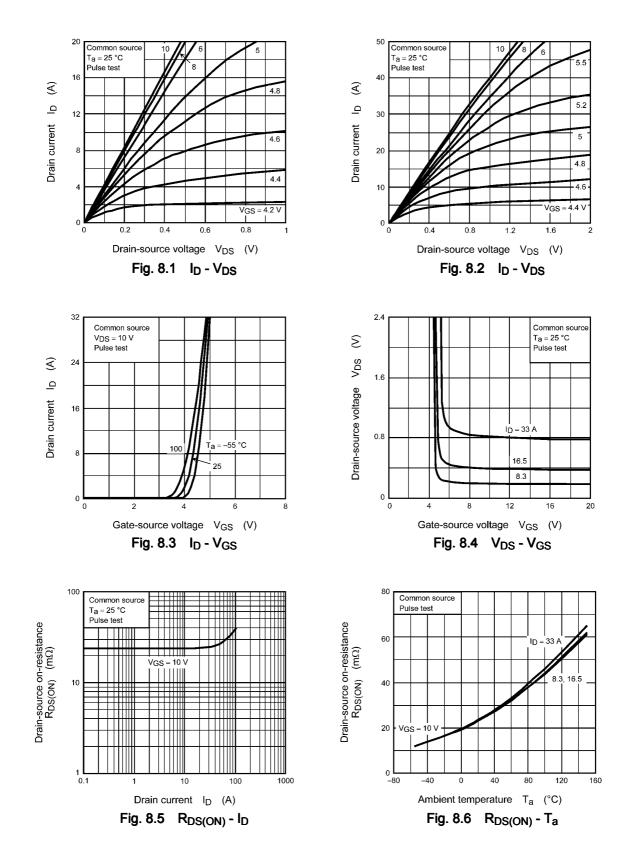
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 6)	I <sub>DRP</sub>	—	_	—	102	Α
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = 33 A, V <sub>GS</sub> = 0 V	_		-1.2	V

Note 6: Ensure that the channel temperature does not exceed 150 °C.

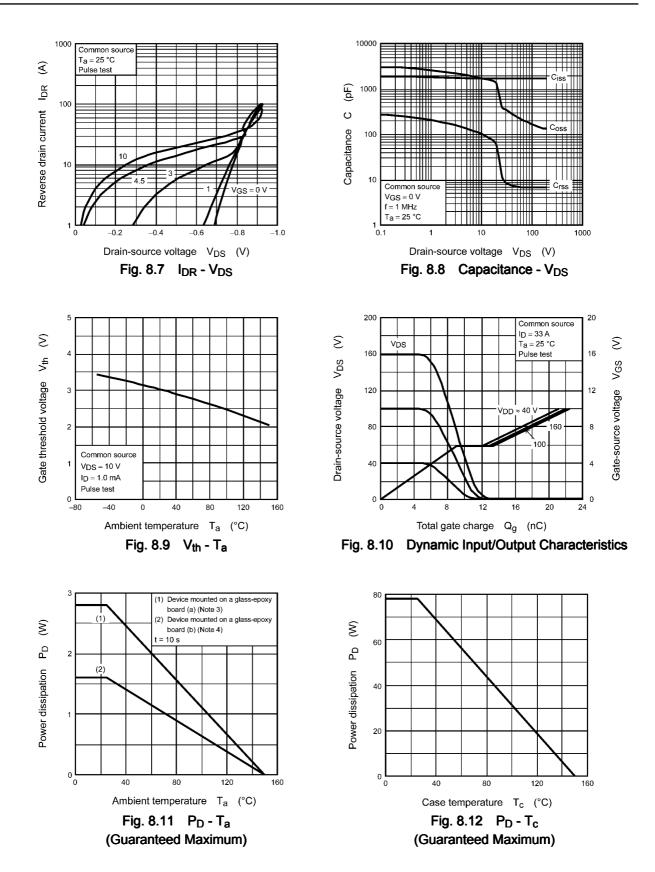
#### 7. Marking



#### 8. Characteristics Curves (Note)



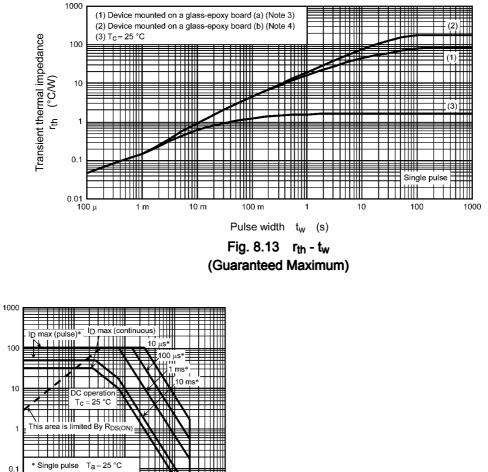


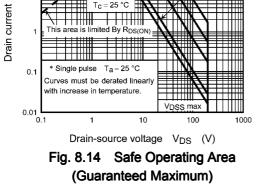




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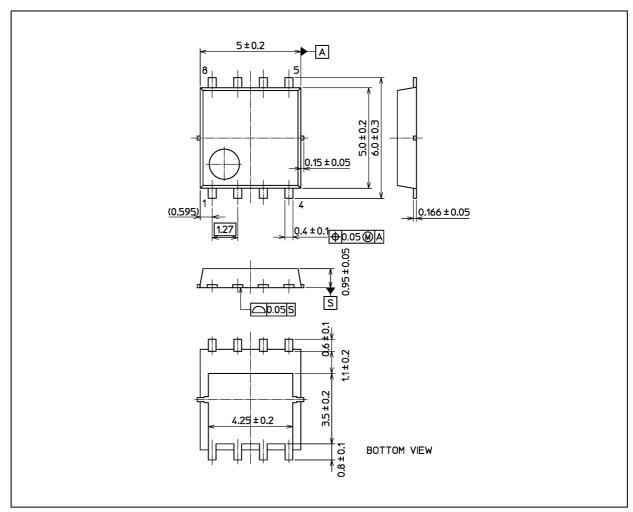


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### TPH2900ENH

#### **Package Dimensions**

Unit: mm



Weight: 0.087 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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